

DOT MATRIX DISPLAY

JZM13882BGO-GW

DATA SHEET

DOCUMENT NO.: WI-RD-LDS-13882BGO-GW

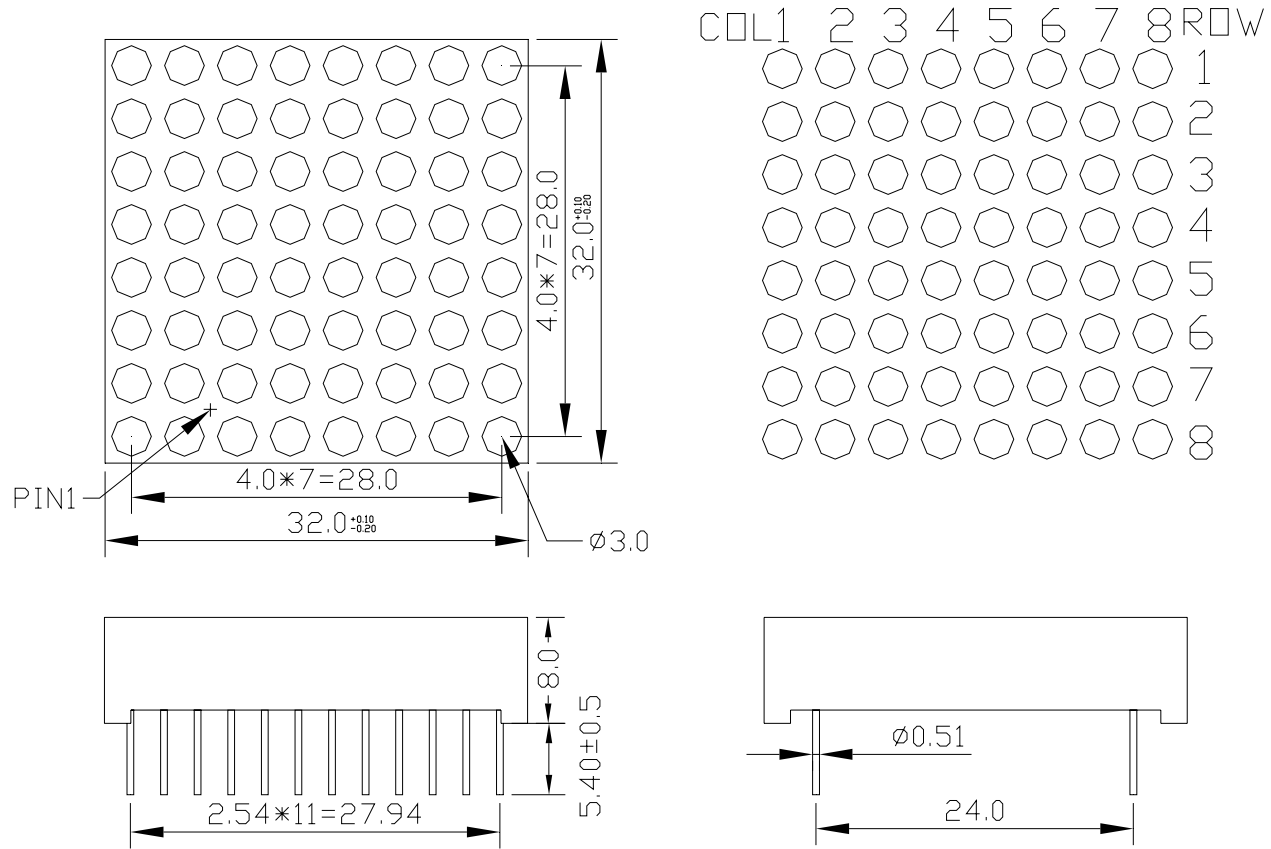
RELEASE DATE: 2007-4-20

VERSION: A/0

RD No.: JZD20070420001

PART NO.: JZM13882BGO-GW

Package Dimensions



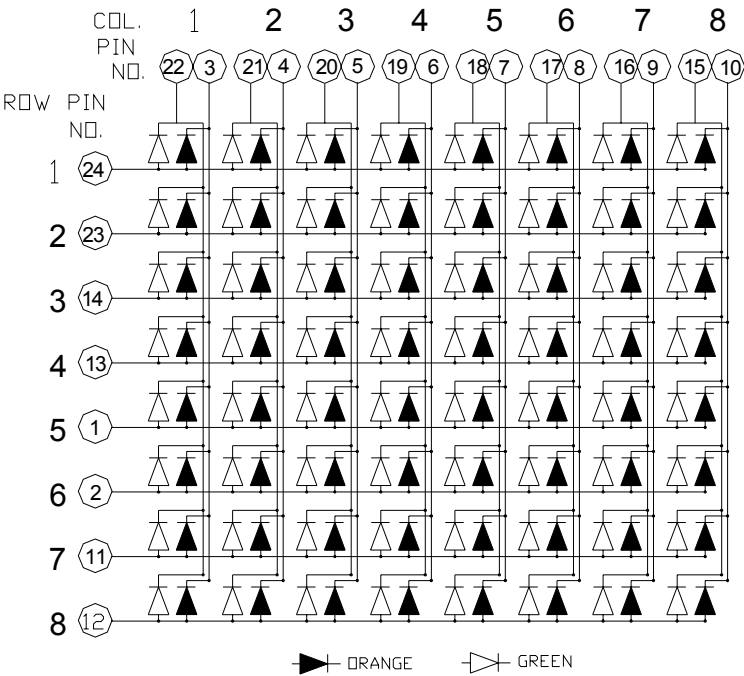
Notes:

- 1. All dimension are in millimeters and(Inch)tolerance is ± 0.25 mm unless otherwise noted.
- 2.Specifications are subject to change without notice.

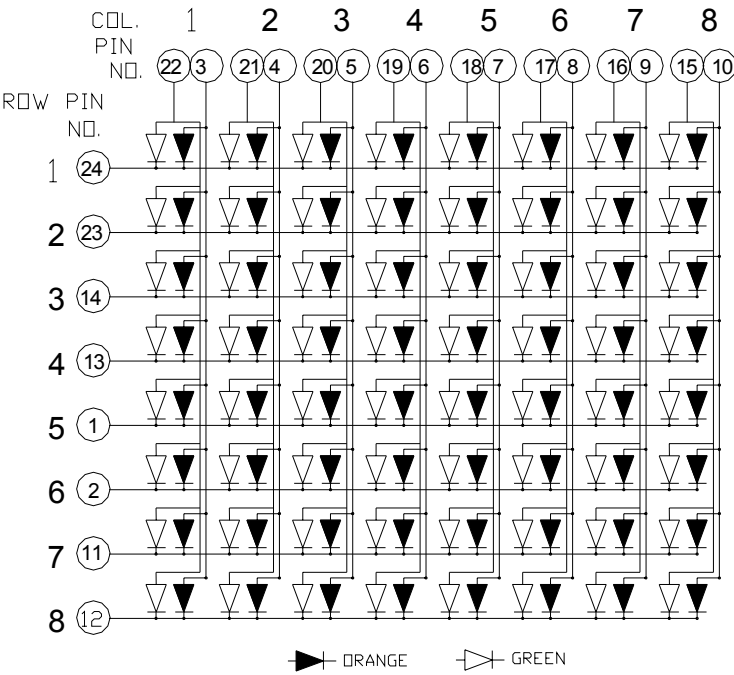
PART NO.: JZM13882BGO-GW

Internal Circuit Diagram

JZM13882AGO-GW



JZM13882BGO-GW



PART NO.: JZM13882BGO-GW

Electrical Connection

PIN NO.	JZM13882AGO-GW	PIN NO.	JZM13882BGO-GW
1	Anode Row 5	1	Cathode Row 5
2	Anode Row 6	2	Cathode Row 6
3	Cathode Column 1 □ORANGE□	3	Anode Column 1 □ORANGE□
4	Cathode Column 2 □ORANGE□	4	Anode Column 2 □ORANGE□
5	Cathode Column 3 □ORANGE□	5	Anode Column 3 □ORANGE□
6	Cathode Column 4 □ORANGE□	6	Anode Column 4 □ORANGE□
7	Cathode Column 5 □ORANGE□	7	Anode Column 5 □ORANGE□
8	Cathode Column 6 □ORANGE□	8	Anode Column 6 □ORANGE□
9	Cathode Column 7 □ORANGE□	9	Anode Column 7 □ORANGE□
10	Cathode Column 8 □ORANGE□	10	Anode Column 8 □ORANGE□
11	Anode Row 7	11	Cathode Row 7
12	Anode Row 8	12	Cathode Row 8
13	Anode Row 4	13	Cathode Row 4
14	Anode Row 3	14	Cathode Row 3
15	Cathode Column 8 □GREEN□	15	Anode Column 8 □GREEN□
16	Cathode Column 7 □GREEN□	16	Anode Column 7 □GREEN□
17	Cathode Column 6 □GREEN□	17	Anode Column 6 □GREEN□
18	Cathode Column 5 □GREEN□	18	Anode Column 5 □GREEN□
19	Cathode Column 4 □GREEN□	19	Anode Column 4 □GREEN□
20	Cathode Column 3 □GREEN□	20	Anode Column 3 □GREEN□
21	Cathode Column 2 □GREEN□	21	Anode Column 2 □GREEN□
22	Cathode Column 1 □GREEN□	22	Anode Column 1 □GREEN□
23	Anode Row 2	23	Cathode Row 2
24	Anode Row 1	24	Cathode Row 1

Absolute Maximum Rating at=Ta=25□

Parameter	Symbol	Ratings	UNIT
		SGM	
Forward Current Per Chip	IF	30	mA
Peak Forward Current Per Chip*1	IFP	100	mA
Power Dissipation Per Chip	PD	100	mW
Reverse Current Per Any Chip	Ir	50	uA
Electrostatic Discharge*2	ESD	1000	V
Operating Temperature	Topr	-25~+85	□
Storage Temperature	Tstg	-25~+85	□

Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260□

*1:Duty 1/10,0.1ms Pulse With

*2:Static Electricity or power surge will damage the LED. Use of a conductive wrist band or anti-electrosatic glove is recommended when handing these LED. All devices, equipment and machinery must be properly grounded.

PART NO.: JZM13882BGO-GW

Part selection And Application Information(Ratings at 25℃)

PART NO.	COLOR □ EPOX Y/SURF ACE□	CHIP		Common cathode or anode	WD (nm)	Electrical				IV- M
		Material	Emitted			Vf(v)		Iv(mcd)		
						Typ.	Max.	Min.	Typ.	
JZM13882BGO-GW	WHITE DIFFUS E/GRAY	GaP/ GaP	GREEN / ORAN GE	Common cathode	572/ 603	2.1/ 1.9	2.4/ 2.4	13/ 13	14/ 14	1 □ 1.1

Note:1.The forward voltage data did not including±.01V testing tolerance.

2.The luminous intensity data did not including±15% testing tolerance.

Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	Vf	volt	If=20mA
Luminous Intensity Per Chip	Iv	mcd	If=20mA
Peak Wavelength	WP	nm	If=20mA
Dominant Wavelength	WD	nm	If=20mA
Spectral Line Half-Width	▲W	nm	If=20mA
Reverse Current Any Chip	Ir	μA	If=20mA
Luminous Intensity Matching Ratio	IV-M		

Typical Optical-Electronic Characteristic Curves

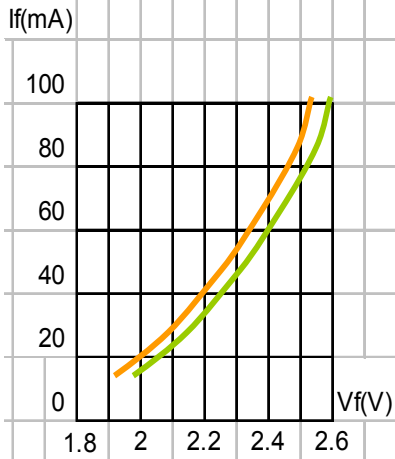
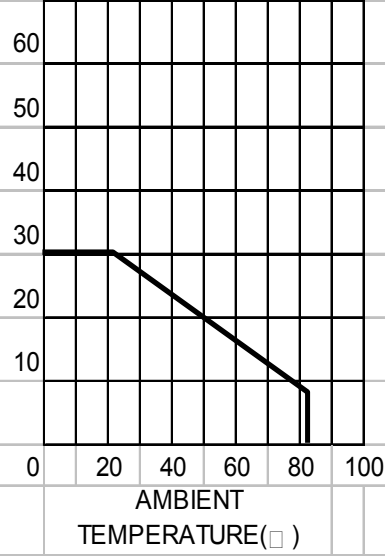


Fig.1 FORWARD CURRENT VS. FORWARD VOLTAGE.

Forward Current@20mA



AMBIENT TEMPERATURE(°C)

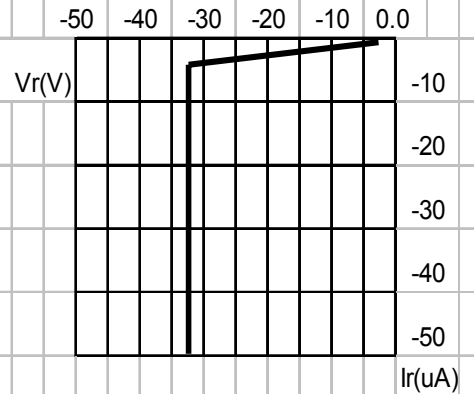


Fig.2 REVERSE CURRENT VS. REVERSE VOLTAGE.

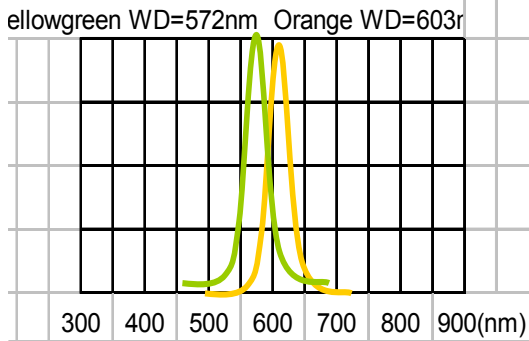


Fig.4 RELATIVE LUMINOUS INTENSITY VS. WAVELENGTH.

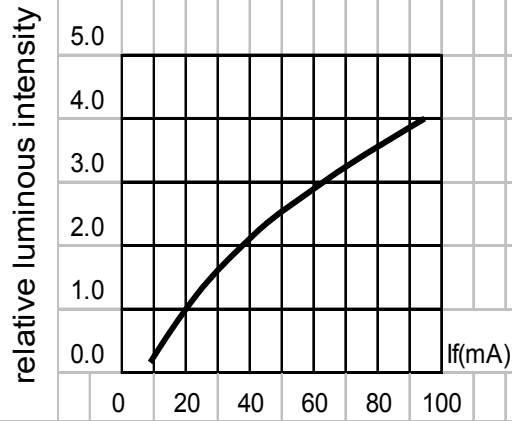


Fig.3 RELATIVE LUMINOUS INTENSITY VS. FORWARD

Soldering Condition (Pb-Free)

1. Iron:

Soldering Iron: 30W Max

Temperature 350°C Max

Soldering Time: 3 Seconds Max (One time only)

Distance: Solder Temperature 1/16Inch Below Seating Plane

For 3 Seconds At 260°C

2. Wave Soldering Profile

Dip Soldering

Preheat: 120°C Max

Preheat time: 60 seconds Max

Ramp-up

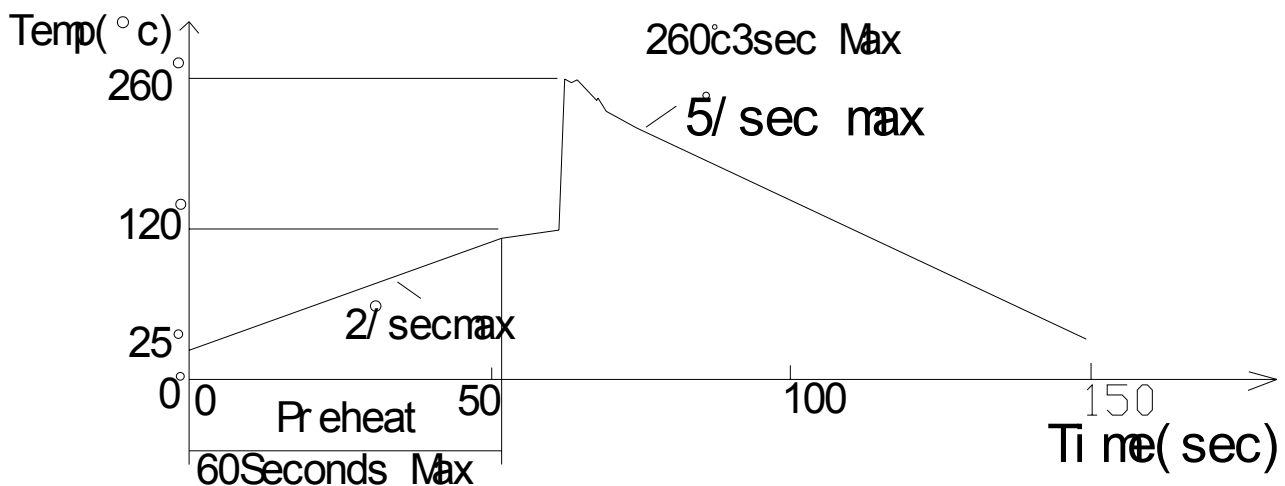
2°C/sec(max)

Ramp-Down: -5°C/sec(max)

Solder Bath: 260°C Max

Dipping Time: 3 seconds Max

Distance: Solder Temperature 1/16Inch Below Seating Plane for 3 Seconds At 260°C



Note: 1. Wave solder should not be made more than one time.

2. You can just only select one of the soldering conditions as above.

Reliability Test:

Test Item	Standard Test Method	Test Condition	Description
Operating Life Test	JIS C7021:B-1 MIL-STD-750:1026 MIL-STD-883:1005	1. Under Room Temperature 2. If=10 mA 3. t=1000hrs(-24hrs,+72hrs)	This test is conducted for the purpose of deteming the resistance of a part in electrical and themal stressed.
High Temperature Storage Test	JIS C 7021:B-10 MIL-STD-883:1008	1. Ta=105□±5□ 2. t=1000hrs(-24hrs,+72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.
Low Temperature Storage Test	JIS C 7021:B-12	1. Ta=-40□±5□ 2. t=1000hrs(-24hrs,+72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.
High Temperature High Humidity Test	JIS C 7021:B-11 MIL-STD-202:103B	1. Ta=65□±5□ 2. RH=90%~95% 3. Tt=240hrs±2hrs	The purpose of this id the resistance of the device which is laid under condition of low temperature for hours.
Thermal Shock Test	MIL-STD-202:107D MIL-STD-750:1051 MIL-STD-883:1011	1. Ta=105□±5□&-40□±5□ (10min)(10min)	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.
Solder Resistance Test	JIS C 7021:A-1 MIL-STD-202:210A MIL-STD-750:2031	1.T.Sol=260□±5□ 2.Dwell time=10±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at ex treme changes in temperature when soldering the lead wire.
Solderability Test	JIS C 7021:A-2 MIL-STD-202:208D MIL-STD-750:2026 MIL-STD-883:2003	1.T.Sol=230□±5□ 2.Dwell time=5±1sec.	This test intended to see soldering well performed or not.

SICHUAN JIUZHOU APPLIED ELECTRONICS CO., LTD.

SHENZHEN JIUZHOU OPTOELECTRONICS CO., LTD.

Jiuzhou Optoelectronics and the Jiuzhou logo are trademarks of Shenzhen Jiuzhou Optoelectronics, Corporation Limited in the People's Republic of China and other countries.

Date subject to change. Copyright©2007 Shenzhen Jiuzhou Optoelectronics Corporation Limited.

All right reserved.